PROCESS CP547

Power Transistor

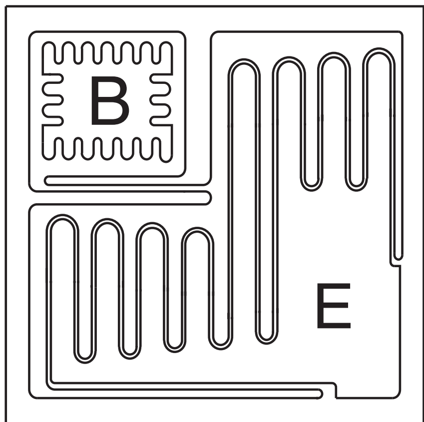
PNP - Darlington Chip

Central™
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL BASE
Die Size	195 X 195 MILS
Die Thickness	12 MILS
Base Bonding Pad Area	29 X 29 MILS
Emitter Bonding Pad Area	61 X 35 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Ti/Ni/Au - 6,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 5 INCH WAFER
290

PRINCIPAL DEVICE TYPES
MJ11011 2N6285
MJ11013 2N6286
MJ11015 2N6287

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

R3 (1-August 2002)

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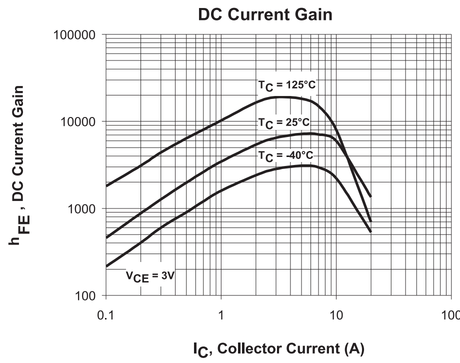
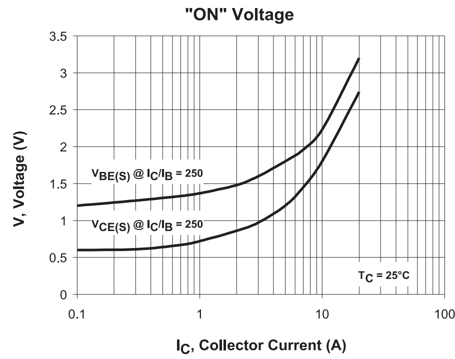
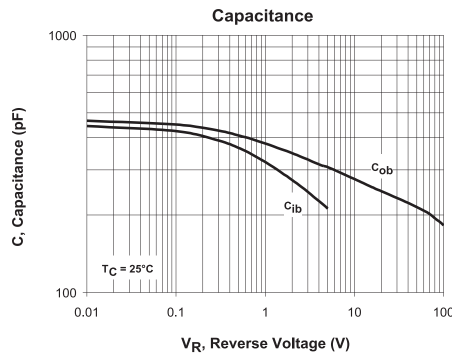
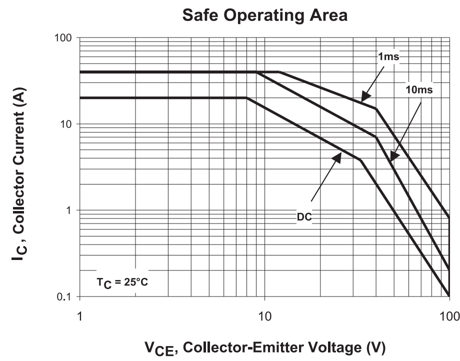
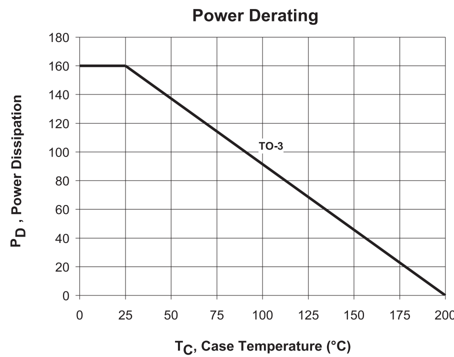
Typical Electrical Characteristics

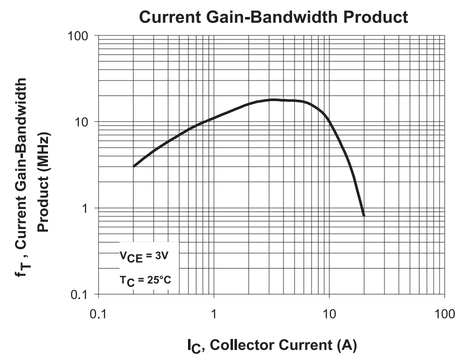












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